

# isc N-Channel MOSFET Transistor

## NTP082N65S3F

#### • FEATURES

- · With TO-220 packaging
- · High speed switching
- · Very high commutation ruggedness
- · Easy to use
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operationz

#### APPLICATIONS

- PFC stages
- UPS
- Power supply
- · Switching applications

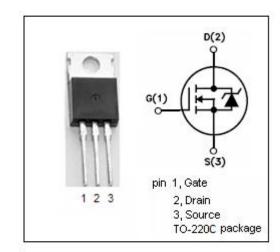


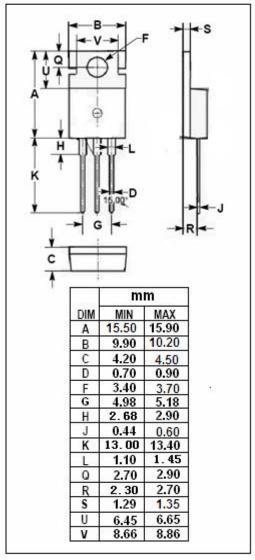
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage		V
V <sub>GSS</sub>	Gate-Source Voltage ±30		V
I <sub>D</sub>	Drain Current-Continuous@Tc=25℃ 40 Tc=100℃ 25.5		А
I <sub>DM</sub>	Drain Current-Single Pulsed	100	А
P <sub>D</sub>	Total Dissipation	313	W
Tj	Operating Junction Temperature -55~150		${}^{\mathbb{C}}$
T <sub>stg</sub>	Storage Temperature -55~		$^{\circ}\!\mathbb{C}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT		
Rth(ch-c)	Channel-to-case thermal resistance	0.4	°C/W		
Rth(ch-a)	Channel-to-ambient thermal resistance	62.5	°C/W		







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =1mA	650			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =4mA	3.0		5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =20A		70	82	mΩ
Igss	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0V			±0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V			10	μА
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =20A, V <sub>GS</sub> = 0 V			1.3	V

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